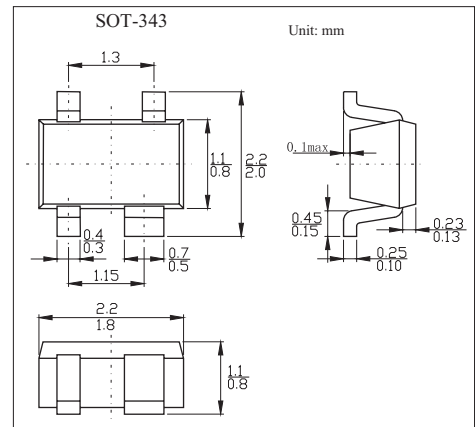


**BAR81W**

■ **Features**

- Design for use in shunt configuration
- High shunt signal isolation
- Low shunt insertion loss



■ **Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	30	V
Forward current	$I_F$	100	mA
Total power dissipation, $T_s = 103^\circ\text{C}$	$P_{tot}$	100	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Operating temperature range	$T_{op}$	-55 to + 125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55 to + 150	$^\circ\text{C}$
Junction - ambient <sup>1)</sup>	$R_{th JA}$	$\leq 200$	K/W
Junction - soldering point	$R_{th JS}$	$\leq 120$	K/W

Note

1. Package mounted on alumina 15mm × 16.7mm × 0.7mm

■ **Electrical Characteristics Ta = 25°C**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse current	$I_R$	$V_R = 20\text{ V}$			20	nA
Forward voltage	$V_F$	$I_F = 100\text{ mA}$		0.93	1	V
Diode capacitance	$C_T$	$V_R = 1\text{ V}, f = 1\text{ MHz}$		0.6		pF
		$V_R = 3\text{ V}, f = 1\text{ MHz}$		0.57		
Forward resistance	$r_f$	$I_F = 5\text{ mA}, f = 100\text{ MHz}$		0.7		$\Omega$
Series inductance	$t_{rr}$			0.15		nH

■ **Marking**

Marking	BBs
---------	-----